

Data Storage at the Nanoscale

Advances and Applications

edited by
Gan Fuxi | Wang Yang



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Preface

Since the mid-1980s, when I got involved in the field of information data storage, I was most interested in optical data storage. I held the International Symposium on Optical Storage (ISOS) in China nine times since 1988 and the International Workshop on Information Storage two times since 2008, and the proceedings were published in SPIE Proceedings, Washington.

New ideas and experiments related to advanced data storage have emerged in recent years, such as quantum storage, atomic storage, and biomolecular storage, which should be encouraged further. I did some work in the field of information data storage in past 10 years, and I am still involved in it. Owing to the requirement of high storage density, the data storage device should work in the nanoscale region. High-density data storage should be green, safe, and long life in the “big data era.”

In this book, I invited several scientists of China to present their research in the field. The book emphasizes more practical methods for data storage development and application. The authors share with the readers their thoughts concerning information data storage at present and in the future.

I thank the authors of this book for their contributions. Also, thanks are due to my colleagues at the Shanghai Institute of Optics and Fine Mechanics, CAS, for their assistance and cooperation, especially to Prof. Wang Yang, the coeditor, for checking and editing all the manuscripts. The editing and publication of this book were also supported under the research grants of the National Natural Science Foundation of China, the National Basic Research Program of China, and the Intellectual Innovation Project of the Chinese Academy of Sciences.

Gan Fuxi

Shanghai, January 2015

Contents

| | |
|----------------|-----|
| <i>Preface</i> | xxi |
|----------------|-----|

1. Overview of Information Data Storage: An Introduction 1

Gan Fuxi

| | | |
|-------|---|----|
| 1.1 | Importance and Research Aims of Information Data Storage | 2 |
| 1.2 | Development Trends of Different Information Storage Devices | 3 |
| 1.2.1 | In-Line Data Storage | 3 |
| 1.2.2 | Storage Class Memory | 5 |
| 1.2.3 | Magnetic Data Storage | 6 |
| 1.2.4 | Rethinking of Optical Data Storage Development | 7 |
| 1.3 | Nanolithography for Information Storage | 9 |
| 1.3.1 | Characteristics of and Requirements for Nanolithography | 9 |
| 1.3.2 | Nanolithography by Optical Means | 9 |
| 1.3.3 | Advanced Optical Lithography | 10 |
| 1.4 | Fast Phase Change | 12 |
| 1.4.1 | Fast Phase Change Initiated by Ultra-Short Laser Pulse | 13 |
| 1.4.2 | New Application of Phase Change Process in Information Data Storage Field | 15 |

2. Super-Resolution Optical Data Storage Using Binary Optics 19

Wang Haifeng and Gan Fuxi

| | | |
|-------|---|----|
| 2.1 | Design of the Super-Resolution Binary Optics | 20 |
| 2.1.1 | Binary Optics Design Based on Scalar Diffraction Theory | 21 |

| | | |
|-----------|--|-----------|
| 2.1.2 | Binary Optics Design Based on Vector Diffraction Theory | 23 |
| 2.2 | Generation of Super-Resolution Longitudinally Polarized Light Beamwith Binary Optics | 26 |
| 2.3 | Application of Binary Optics to Near-Field Recording | 28 |
| 2.3.1 | System Configuration for Circular Polarized Light | 28 |
| 2.3.2 | System Configuration for Longitudinally Polarized Light | 31 |
| 2.3.3 | Near-Field Recording Using Optical Antennas | 33 |
| 3. | Focal Spot Engineering for Bit-by-Bit Recording | 39 |
| | <i>Gan Xiaosong and Wu Jingzhi</i> | |
| 3.1 | Introduction | 39 |
| 3.2 | Far-Field Modulation for Super-Resolution Focal Spot | 41 |
| 3.3 | Saturation Microscopy | 47 |
| 3.4 | Breaking the Diffraction Limit Without Diffraction? | 50 |
| 3.5 | Discussion | 53 |
| 4. | Plasmonic Nanofocusing and Data Storage | 59 |
| | <i>Cao Qing</i> | |
| 4.1 | Surface Plasmon and Its Properties | 59 |
| 4.1.1 | Surface Plasmons | 59 |
| 4.1.2 | Enhanced Transmission | 61 |
| 4.1.3 | Metal Wire Surface Plasmon | 62 |
| 4.1.4 | Surface Plasmon Laser | 63 |
| 4.1.5 | Graphene Plasmon | 64 |
| 4.2 | Plasmonic Nanofocusing and Nanoimaging | 64 |
| 4.2.1 | Tapered Structure | 64 |
| 4.2.2 | Multiple Concentric Groove Metallic Lens | 67 |
| 4.2.3 | Metal Films for Super-Diffraction-Limited Imaging | 68 |

| | | |
|-----------|---|-----------|
| 4.3 | Plasmonic Data Storage at the Nanoscale | 70 |
| 4.3.1 | Brief Introduction of High-Density Optical Data Storage | 70 |
| 4.3.2 | Two Basic Concepts of Plasmonic Data Storage | 71 |
| 4.3.2.1 | High-density data storage technology mixed with plasmonic near-field transducers and bit-patterned magnetic materials | 71 |
| 4.3.2.2 | Five-dimensional optical recording mediated by surface plasmons in gold nanorods | 72 |
| 4.4 | Plasmonic Nanolithography | 74 |
| 4.4.1 | Brief Introduction of Plasmonic Nanolithography | 74 |
| 4.4.2 | Plasmonic Contact Lithography | 75 |
| 4.4.3 | Imaging Lithography of Planar Lens | 76 |
| 4.4.4 | Plasmonic Direct Writing Nanolithography | 77 |
| 5. | Nano-Optical Data Storage with Nonlinear Super-Resolution Thin Films | 91 |
| | <i>Wei Jingsong and Gan Fuxi</i> | |
| 5.1 | Introduction | 92 |
| 5.2 | The Principle of Nonlinear Super-Resolution Nano-Optical Data Storage | 93 |
| 5.3 | Optical Response of the Nonlinear Layer | 94 |
| 5.3.1 | Nonlinear Response of Sb-Based Phase Change Thin Films | 95 |
| 5.3.2 | Nonlinear Response of Metal Doped Semiconductor Thin Films | 98 |
| 5.3.2.1 | The sample preparation | 98 |
| 5.3.2.2 | Measurement of the optical nonlinear properties | 100 |
| 5.3.2.3 | The mechanism of nonlinear response | 102 |
| 5.4 | The Formation of Super-Resolution Optical Spot | 107 |

| | | |
|-----------|--|------------|
| 5.4.1 | Theoretical Basis of Super-Resolution Spot Formation | 107 |
| 5.4.2 | Super-Resolution Spot Formation by Ag Doped Si Thin Films | 109 |
| 5.4.3 | Super-Resolution Spot Formation by Sb-Based Phase Change Thin Films | 112 |
| 5.5 | Experimental Results of the Nano-Optical Data Recording and Readout | 114 |
| 5.6 | On the Dynamic Readout Characteristic of the Nonlinear Super-Resolution Thin Films | 120 |
| 5.6.1 | Theoretical Analysis of the Dependence of Readout Threshold Power on Mark Size | 120 |
| 5.6.2 | Dependence of Readout Characteristic on Laser Power | 122 |
| 5.6.3 | Dependence of Readout Characteristic on Laser Irradiation Time | 123 |
| 5.6.4 | Analysis of the Influence of Laser Energy on Dynamic Readout Characteristic | 126 |
| 5.7 | Conclusion | 128 |
| 6. | Mastering Technology for High-Density Optical Disc | 131 |
| | <i>Geng Yongyou and Wu Yiqun</i> | |
| 6.1 | Introduction | 131 |
| 6.2 | Major Mastering Technologies for High-Density Optical Disc | 135 |
| 6.2.1 | Electron Beam Recording | 135 |
| 6.2.2 | UV and DUV Recording | 138 |
| 6.2.3 | Near-Field Optical Recording | 140 |
| 6.2.4 | Laser Thermal Recording | 143 |
| 6.2.4.1 | Mechanism of laser thermal recording | 143 |
| 6.2.4.2 | Materials for laser thermal recording | 144 |
| 6.2.4.3 | Writing strategy for laser thermal recording | 162 |
| 6.2.5 | STED Recording | 163 |

| | | |
|-----------|---|------------|
| 6.2.5.1 | Principle of STED microscopy | 163 |
| 6.2.5.2 | Applications in nanorecording | 164 |
| 6.3 | Conclusion | 166 |
| 7. | Laser-Induced Phase Transition and Its Application in Nano-Optical Storage | 171 |
| | <i>Wang Yang and Gan Fuxi</i> | |
| 7.1 | Introduction: Phenomena and Applications of Laser-Induced Phase Transition in the Optical Storage | 171 |
| 7.1.1 | Amorphous and Crystalline States for Binary Memory | 173 |
| 7.1.2 | Transient States for Self-Masking Super-Resolution | 174 |
| 7.1.3 | Meta-Stable Multi-States for Multilevel Recording | 176 |
| 7.2 | Physical Process of Laser-Induced Phase Transition | 177 |
| 7.3 | Probing Method for Laser-Induced Phase Transition Process | 182 |
| 7.4 | Phase Transition Dynamics Driven by Laser Pulses | 185 |
| 7.4.1 | Carrier Dynamics Driven by Ultrashort Laser Pulses | 185 |
| 7.4.2 | Laser Pulse-Induced Amorphization Process | 190 |
| 7.4.3 | Laser Pulse-Induced Crystallization Process | 194 |
| 7.4.3.1 | Comparison of optical and electrical transient response during nanosecond laser pulse-induced crystallization | 194 |
| 7.4.3.2 | Optical transients during the picosecond laser pulse-induced crystallization: comparison of nucleation-driven and growth-driven processes | 198 |

| | | |
|-----------|---|------------|
| 7.4.3.3 | Optical transients during the femtosecond laser pulse-induced crystallization | 206 |
| 7.5 | Phase-Change Optical Disk Technology | 213 |
| 7.6 | New Optical Memory Functions Based on Phase-Change Materials | 221 |
| 7.6.1 | Fast Cycling Driven by Ultrashort Laser Pulses with Identical Fluences | 221 |
| 7.6.2 | Optical-Electrical Hybrid Operation for Phase-Change Materials | 224 |
| 7.6.3 | Metal-Nanoparticle-Embedded Phase-Change Recording Pits for Plasmonics and Super-Resolution | 226 |
| 7.6.4 | Polarization Readout for Multilevel Phase-Change Recording by Crystallization Degree Modulation | 232 |
| 7.6.5 | Polarized Laser-Induced Dichroism of Phase-Change Materials | 239 |
| 7.6.6 | Fluorescence Multi-States of Ion-Doped Phase-Change Thin Films | 246 |
| 8. | SPIN-Based Optical Data Storage | 259 |
| | <i>Gu Min, Cao Yaoyu, Li Xiangping, and Gan Zongsong</i> | |
| 8.1 | SPIN Based on Single-Photon Photoinduction | 264 |
| 8.1.1 | Theoretical Model of the SPIN Process | 264 |
| 8.1.2 | Experimental Demonstration of Single-Photon SPIN | 267 |
| 8.2 | SPIN Based on Two-Photon Photoinduction | 270 |
| 8.2.1 | Experimental Demonstration of Two-Photon SPIN | 271 |
| 8.2.2 | Properties and Limitations | 276 |
| 8.3 | Conclusion | 278 |
| 9. | Magnetic Random Access Memory | 281 |
| | <i>Han Xiufeng and Syed Shahbaz Ali</i> | |
| 9.1 | History of the Development of MRAM Devices | 281 |
| 9.2 | MRAM Devices Based on GMR/AMR Effects | 287 |

| | | |
|--------|---|-----|
| 9.3 | Field-Write Mode MRAM Based on TMR Effect | 290 |
| 9.3.1 | Astroid-Mode MRAM | 292 |
| 9.3.2 | Principles of Astroid-Mode MRAM | 293 |
| 9.3.3 | Development of Astroid-Mode MRAM | 294 |
| 9.3.4 | Toggle-Mode MRAM | 296 |
| 9.3.5 | Principles of Toggle-Mode MRAM | 297 |
| 9.3.6 | Write-Current Reduction in Toggle-Mode MRAM | 298 |
| 9.3.7 | Energy Diagram of Toggle Operation | 301 |
| 9.3.8 | Competitive Market | 306 |
| 9.3.9 | MRAM Based on Vertical Current Writing and Its Control Method | 306 |
| 9.3.10 | Field-Write Mode MRAM Chip-Design | 307 |
| 9.4 | Spin Transfer Torque MRAM Based on Nanoscale Magnetic Tunnel Junction MTJ | 309 |
| 9.4.1 | Spin Transfer Torque Effects | 312 |
| 9.4.2 | STT Effects in a Multilayer Thin-Film Stack | 313 |
| 9.4.3 | STT MRAM with an in-Plane Magnetic Configuration | 315 |
| 9.4.4 | Switching Characteristics and Threshold in MTJs | 316 |
| 9.4.5 | Switching Probability in the Thermal Regime | 317 |
| 9.4.6 | STT MRAM with a Perpendicular Magnetic Configuration | 318 |
| 9.4.7 | Principles of STT-MRAM with a Perpendicular Magnetic Configuration | 319 |
| 9.4.8 | Reliability of Tunnel Barriers in MTJs | 322 |
| 9.4.9 | Write-Current Reduction | 323 |
| 9.4.10 | Current-Write Mode MRAM Chip-Design | 325 |
| 9.4.11 | Introduction of the STT-MRAM Chip Design | 327 |
| 9.5 | Asymmetric MTJ Switching | 329 |

| | | |
|-------|---|-----|
| 9.6 | Nanoring and Nano-Elliptical Ring-Shaped MTJ-Based MRAM | 331 |
| 9.7 | Thermally Assisted Field Write in MRAM | 334 |
| 9.7.1 | Self-Referenced MRAM | 338 |
| 9.8 | Outlook to the Future MRAM | 339 |
| 9.8.1 | Separated Read and Write Operation MRAM | 340 |
| 9.8.2 | Domain Wall Motion MRAM | 340 |
| 9.8.3 | Rashba Effect/Spin-Orbital Coupling Effect Based MRAM | 342 |
| 9.8.4 | Spin Hall Effect-Based MRAM | 344 |
| 9.8.5 | Electric Field Switching MRAM | 346 |
| 9.8.6 | Roadmap of MRAM Demo Device Development | 348 |

10. RRAM Device and Circuit 363

Lin Yinyin, Song Yali, and Xue Xiaoyong

| | | |
|----------|--|-----|
| 10.1 | Introduction | 363 |
| 10.2 | RRAM Cell | 368 |
| 10.2.1 | 1T1R Cell with Transistor as Selector Device | 368 |
| 10.2.1.1 | 1T1R cell structure | 368 |
| 10.2.1.2 | Bipolar and unipolar operation | 372 |
| 10.2.2 | Cell Using Diode as Selector Device | 374 |
| 10.2.2.1 | 1D1R cell with traditional one-directional diode as selector device for unipolar operation | 374 |
| 10.2.2.2 | 1BD1R cell with bidirectional diode as selector device in support of both bipolar and unipolar operation | 376 |
| 10.2.3 | Self-Selecting RRAM Cell | 379 |
| 10.2.3.1 | Hybrid memory | 379 |
| 10.2.3.2 | Complementary-RRAM | 382 |

| | | |
|----------|---|-----|
| 10.3 | Resistive Switching Mechanism | 383 |
| 10.3.1 | ITRS Categories of RRAM | 383 |
| 10.3.2 | Resistive Switching Behavior | 387 |
| 10.3.3 | Forming and SET Process | 388 |
| 10.3.4 | Filament Type | 389 |
| 10.3.5 | Filament Size and the Scaling Characteristics | 391 |
| 10.4 | Influencing Factors and Optimization of RRAM Performance | 393 |
| 10.4.1 | Decrease of Switching Current | 393 |
| 10.4.1.1 | Multilayer architecture | 395 |
| 10.4.1.2 | Control of the compliance current | 397 |
| 10.4.2 | Enhancement of Uniformity | 398 |
| 10.4.2.1 | Electrode effects | 399 |
| 10.4.2.2 | Buffer layer inserting and bilayer construct | 400 |
| 10.4.2.3 | Embedded metal to control conductive path | 401 |
| 10.4.2.3 | Programming algorithm | 402 |
| 10.5 | RRAM Reliability | 403 |
| 10.5.1 | The Retention Test Method | 403 |
| 10.5.2 | Retention Model and Improvement Methods | 404 |
| 10.5.2.1 | RRAM retention failure model | 404 |
| 10.5.2.2 | Retention improvement by forming high-density V_o | 405 |
| 10.5.2.3 | Retention improvement by dynamic self-adaptive write method | 406 |
| 10.5.3 | Endurance Model and Improvement Methods | 408 |
| 10.5.3.1 | Endurance failure model | 408 |
| 10.5.3.2 | High-endurance cell architecture | 411 |

| | | | |
|------|----------|--|-----|
| | 10.5.3.3 | Enhancement of endurance by programming algorithm | 414 |
| 10.6 | | Circuit Techniques for Fast Read and Write | 415 |
| | 10.6.1 | Current SA for High-Speed Read | 415 |
| | 10.6.1.1 | Feedback-regulated bit line biasing approach | 416 |
| | 10.6.1.2 | Process-temperature-aware dynamic BL-bias scheme | 417 |
| | 10.6.2 | Fast Verify for High-Speed Write | 418 |
| 10.7 | | Yield and Reliability Enhancement Assisted by Circuit | 420 |
| | 10.7.1 | Circuit Techniques to Improve Read Yield | 420 |
| | 10.7.1.1 | Parallel-series reference cell | 421 |
| | 10.7.1.2 | SARM reference | 421 |
| | 10.7.1.3 | Body-drain-driven current sense amplifier | 422 |
| | 10.7.1.4 | Temperature-aware bit line biasing | 423 |
| | 10.7.2 | Circuit-Assisted Write Yield Improvement and Operation Power Reduction | 425 |
| | 10.7.2.1 | Self-adaptive write mode | 426 |
| | 10.7.2.2 | Self-timing write with feedback | 427 |
| | 10.7.3 | Circuit-Assisted Endurance and Retention Improvement | 428 |
| | 10.7.3.1 | Filament scaling forming technique and level-verify-write scheme | 428 |
| | 10.7.3.2 | Dynamic self-adaptive write method | 431 |
| 10.8 | | Circuit Strategies for 3D RRAM | 432 |
| | 10.8.1 | Sneaking Path and Large Power Consumption of Conventional Cross-Bar Architecture | 434 |
| | 10.8.2 | 3D RRAM Based on 1TXR Cell without Access Transistor | 435 |
| | 10.8.2.1 | 1TXR cell | 436 |

| | | |
|------------|---|------------|
| 10.8.2.2 | Array architecture | 437 |
| 10.8.2.3 | Write algorithm to inhibit write disturbance | 438 |
| 10.8.2.4 | Read algorithm to inhibit read disturbance | 441 |
| 10.8.3 | 3D RRAM Based on 1D1R Cell | 442 |
| 10.8.3.1 | Array architecture | 442 |
| 10.8.3.2 | Write circuit with leakage compensation for accurate state-change detection | 443 |
| 10.8.3.3 | Read circuit with bit line capacitive isolation for fast swing in SA | 444 |
| 10.8.4 | 3D RRAM Based on 1BD1R | 445 |
| 10.8.4.1 | Array architecture | 445 |
| 10.8.4.2 | Programming conditions for 1BD array | 446 |
| 10.8.4.3 | Multi-bit write architecture with write dummy cell | 447 |
| 10.8.5 | Vertical Stack with Cost Advantage of Lithography | 448 |
| 10.8.5.1 | Cross section of cell and array | 448 |
| 10.8.5.2 | Integration | 450 |
| 10.8.5.3 | Cost advantage of lithography | 451 |
| 11. | Phase-Change Random Access Memory | 463 |
| | <i>Liu Bo</i> | |
| 11.1 | Introduction | 464 |
| 11.2 | Principle of PCRAM | 465 |
| 11.3 | Comparisons between PCRAM and SRAM, DRAM and Flash | 467 |
| 11.4 | History of PCRAM R&D | 470 |
| 11.5 | Phase-Change Material | 474 |
| 11.5.1 | Materials Selective Method | 474 |

| | | |
|------------|--|------------|
| 11.5.2 | GeSbTe System | 476 |
| 11.5.3 | SbTe-Based Materials | 483 |
| 11.5.4 | SiSbTe System | 487 |
| 11.5.5 | GeTe System | 496 |
| 11.5.6 | Sb-Based Materials | 498 |
| 11.5.7 | Nano-Composite Phase-Change Materials | 501 |
| 11.5.8 | Superlattice-Like Structure Phase-Change Materials | 503 |
| 11.6 | Memory Cell Selector | 506 |
| 11.6.1 | Overview | 506 |
| 11.6.2 | Diode | 510 |
| 11.7 | Memory Cell Resistor Structure | 514 |
| 11.8 | Processing | 517 |
| 11.8.1 | Deposition of Phase-Change Materials | 517 |
| 11.8.2 | Etching of Phase-Change Materials | 519 |
| 11.8.3 | Chemical Mechanical Polishing of Phase-Change Materials | 523 |
| 11.9 | Characteristics of PCRAM Memory Cell | 528 |
| 11.9.1 | Reduction of Operation Current/Voltage | 528 |
| 11.9.2 | Reliability | 539 |
| 11.9.3 | Data Retention | 543 |
| 11.9.4 | Speed | 544 |
| 11.10 | Future Outlook | 546 |
| 11.10.1 | Scaling Properties | 547 |
| 11.10.2 | Multi-Bit Operation | 549 |
| 11.10.3 | Three-Dimensional Integration | 552 |
| 11.11 | Potential Application of PCRAM | 553 |
| 12. | Nano-DRAM Technology for Data Storage Application | 591 |
| | <i>Wang Pengfei and Zhang David Wei</i> | |
| 12.1 | Introduction to DRAM Cell Technology | 592 |
| 12.1.1 | Cell Operation of DRAM Cell | 592 |
| 12.1.2 | DRAM Device and Array Structure | 594 |